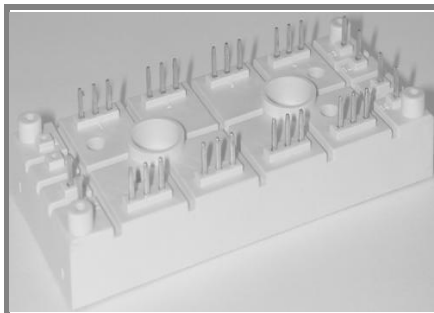


SKDH 116/.. -L100



SEMIPONT™ 6

3-Phase Bridge Rectifier + IGBT braking chopper

SKDH 116/.. -L100

Preliminary Data

Features

- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

Typical Applications

- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger

DH

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 110$ A (maximum value for continuous operation) ($T_s = 80$ °C)
1300	1200	SKDH 116/12-L100
1700	1600	SKDH 116/16-L100

Absolute Maximum Ratings		$T_s = 25$ °C, unless otherwise specified		
Symbol	Conditions	Values	Units	
Bridge - Rectifier				
I_D	$T_s = 80$ °C; inductive load	110	A	
I_{FSM}/I_{TSM}	$t_p = 10$ ms; sin 180 ; T_{jmax}	950	A	
i^2t	$t_p = 10$ ms; sin 180 ; T_{jmax}	4500	A ² s	
IGBT - Chopper				
V_{CES}/V_{GES}		1200 / 20	V	
I_C	$T_s = 25$ (70) °C	125 (100)	A	
I_{CM}	$t_p = 1$ ms; $T_s = 25$ (70) °C	250 (200)	A	
Freewheeling - CAL Diode				
V_{RRM}		1200	V	
I_F	$T_s = 25$ (70) °C	130 (90)	A	
I_{FM}	$t_p = 1$ ms; $T_s = 25$ (70) °C	240 (180)	A	
T_{vj}	Diode & IGBT (Thyristor)	- 40 ... + 150 (-40...+ 125)		°C
T_{stg}		- 40 ... + 125		°C
T_{solder}	terminals, 10 s	260		°C
V_{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600		V

Characteristics		$T_s = 25$ °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
Diode - Rectifier					
V_{TO} / r_t	$T_j = 125$ °C	0,8 / 7			V / mΩ
$R_{th(j-s)}$	per diode			1	K/W
Thyristor - Rectifier					
$V_{F(TO)} / r_t$	$T_j = 125$ °C	1,1 / 6			V / mΩ
$R_{th(j-s)}$	per Thyristor			0,85	K/W
I_{GD}	$T_j = 125$ °C; d.c.	5			mA
V_{GT} / I_{GT}	$T_j = 25$ °C			3 / 150	V / mA
I_H / I_L	$T_j = 25$ °C	250 / 600			mA
$(dv/dt)_{cr}$	$T_j = 125$ °C			1000	V/μs
$(di/dt)_{cr}$	$T_j = 125$ °C			100	A/μs
IGBT - Chopper					
$V_{CE(sat)}$	$I_C = 100$ A, $T_j = 25$ °C; $V_{GE} = 15$ V	2,35			V
$R_{th(j-s)}$	per IGBT			0,3	K/W
$t_{d(on)} / t_r$	valid for all values: $V_{CC} = 600$ V; $V_{GE} = 15$ V;	114 / 94,5			ns
$t_{d(off)} / t_f$	$I_C = 120$ A; $T_j = 125$ °C;	845,4 / 94,5			ns
$E_{on} + E_{off}$	$T_j = 125$ °C; $R_G = 16$ Ω; inductive load	24,4			mJ
CAL - Diode - Freewheeling					
$V_{T(TO)} / r_t$	$T_j = 125$ °C	1 / 8	1,2 / 11		V / mΩ
$R_{th(j-s)}$	per diode			0,6	K/W
I_{RRM}	valid for all values:	65			A
Q_{rr}	$I_F = 100$ A; $V_R = - -600$ V; $di_F/dt = - -1000$ A/μs	15			μC
E_{off}	$V_{GE} = 0$ V; $T_j = 125$ °C				mJ
Temperature Sensor					
R_{TS}	$T = 25$ (100) °C;	1000 (1670)			Ω
Mechanical data					
M_S	mounting Torque	2,55	3,45		Nm

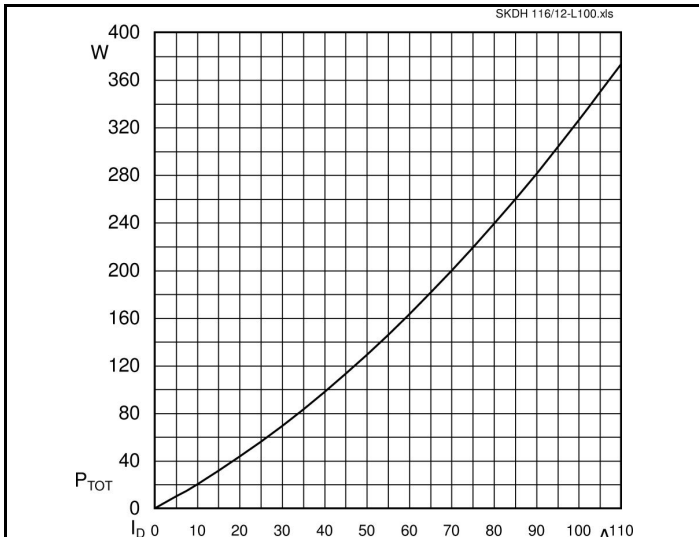


Fig. 1 Power dissipation per module vs. output current

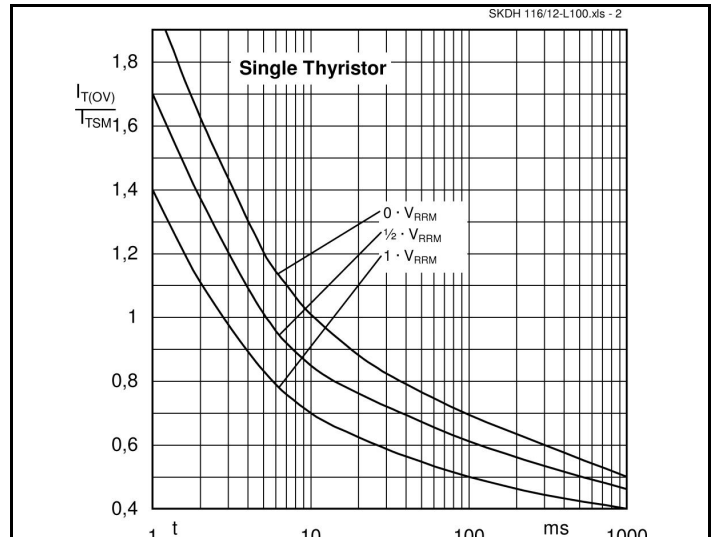


Fig. 2 Surge overload current vs. time

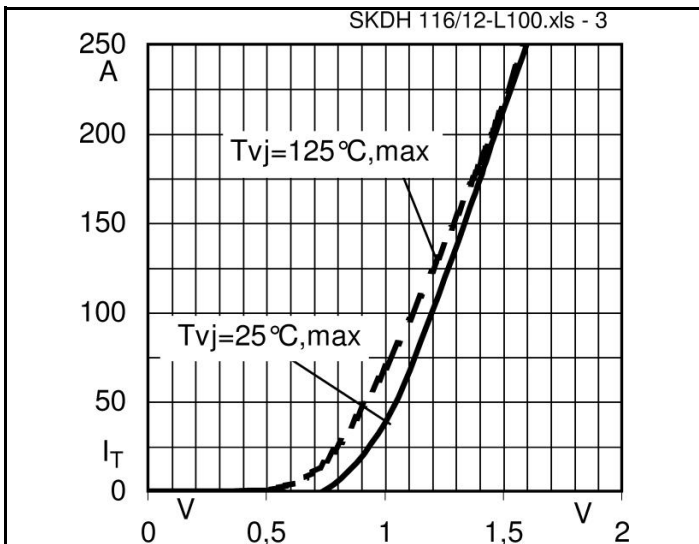


Fig. 3 Forward characteristic of single rectifier diode

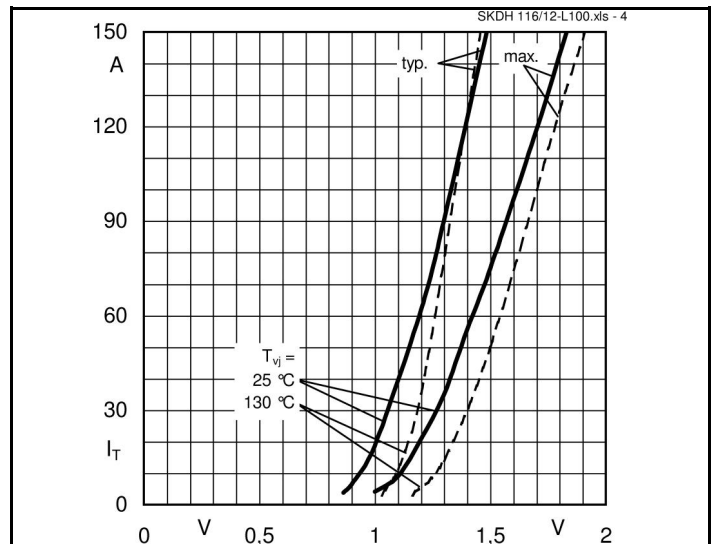


Fig. 4 Forward characteristic of single thyristor

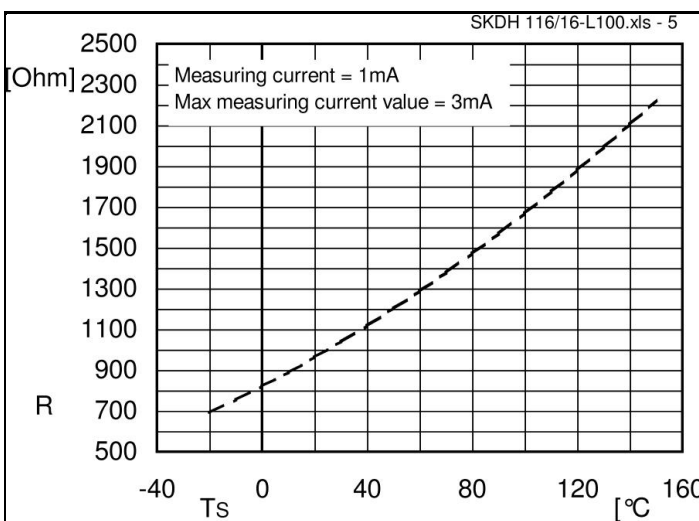


Fig. 5 Temperature sensor characteristic

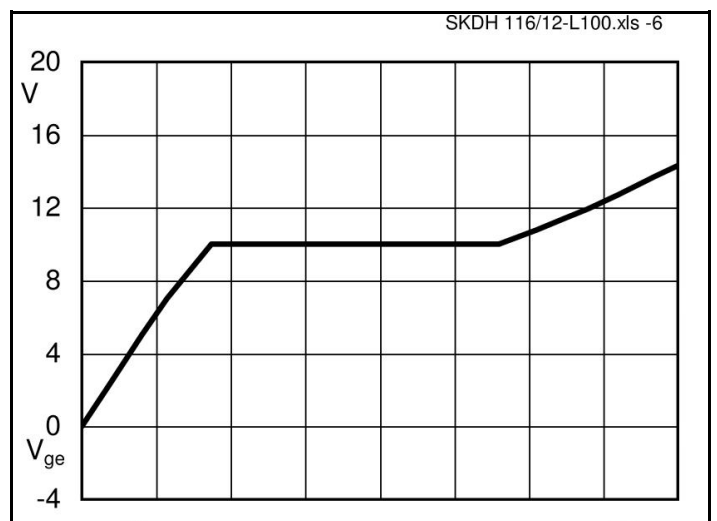
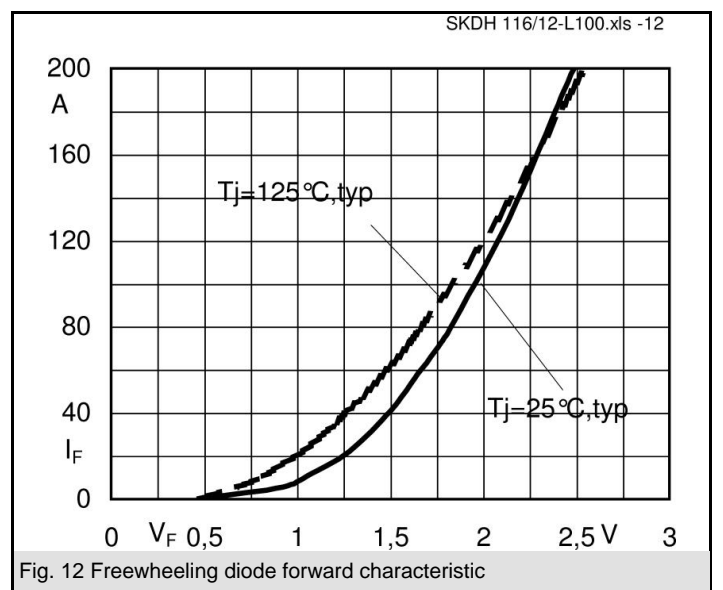
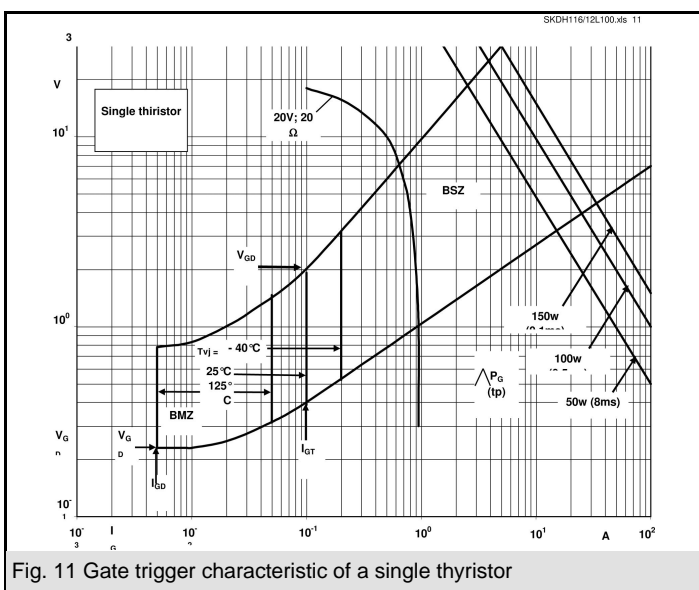
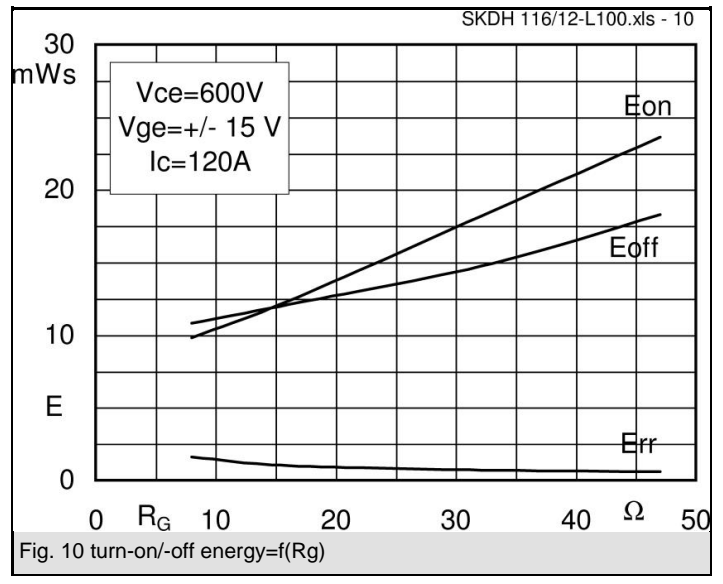
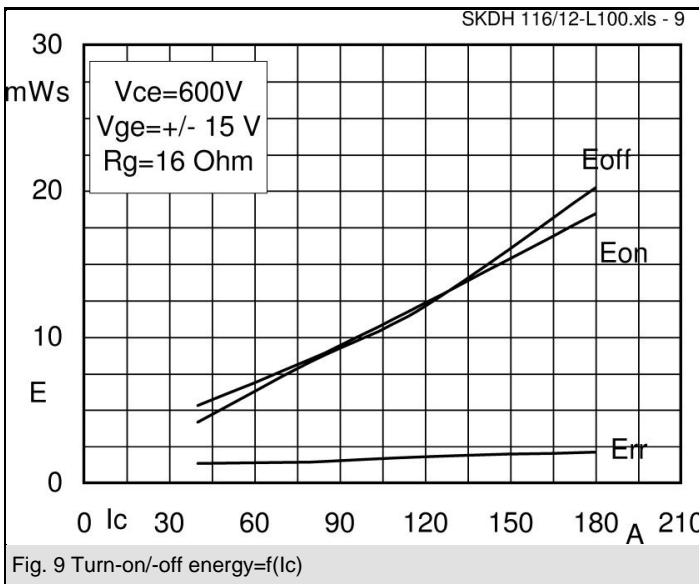
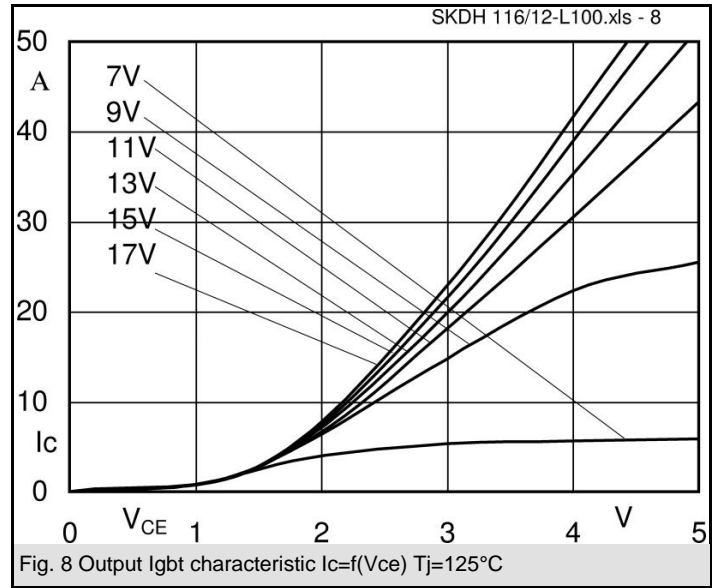
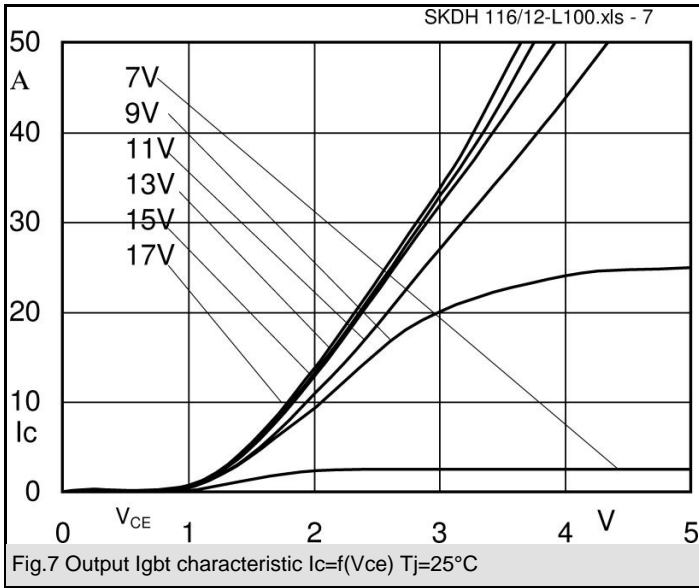


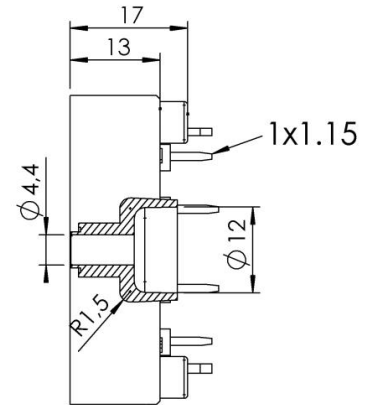
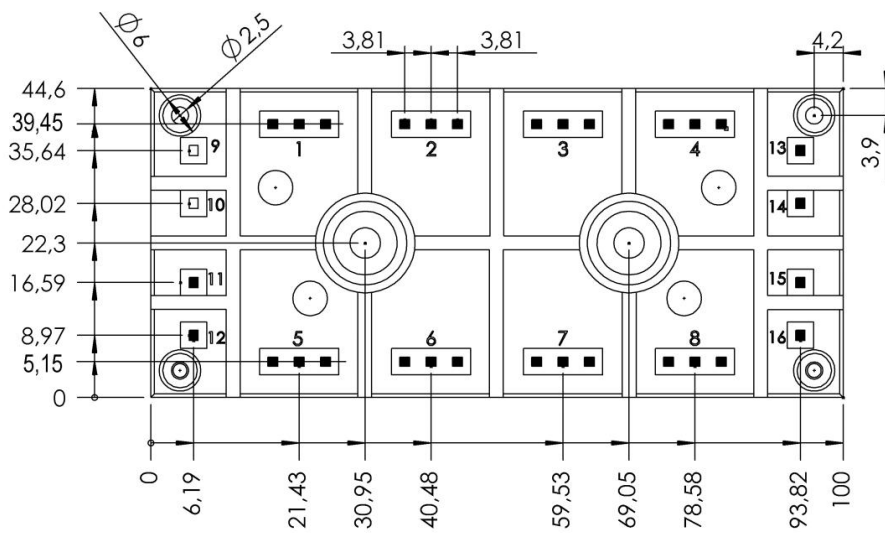
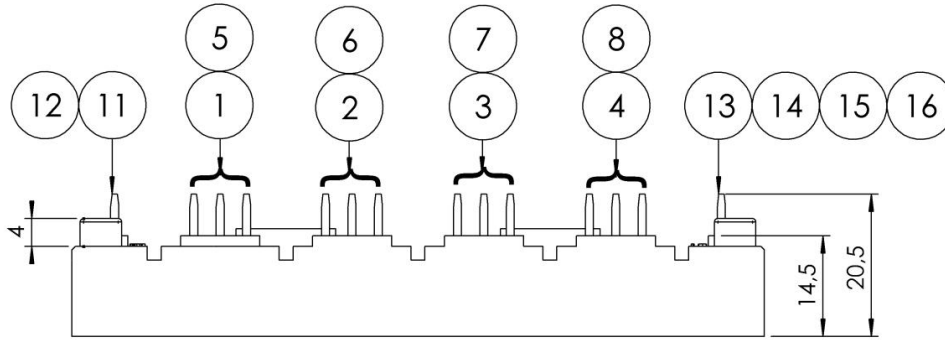
Fig. 6 Typ gate charge characteristic



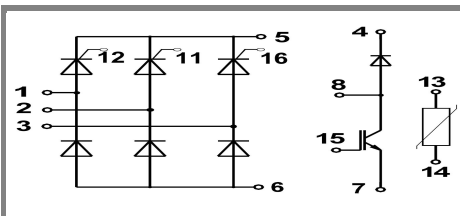
SKDH 116/.. -L100

UL recognized
File n#176; E63 532

Dimensions in mm



Case G 59



Case G 59

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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